



INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.

ITO.0045US (P16093)

SERIAL NO.

10/634,130

APPLICANT(S):

Brian G. Johnson et al.

FILING DATE:

August 4, 2003

GROUP ART UNIT:

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TL	A.	4,115,872	09/19/1978	Bluhm			
	B.	4,366,614	01/04/1983	Kumurdjian			
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	D.	5,789,758	08/04/1998	Reinberg			
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TL	G.	2003/0116794	06/26/2003	Lowrey			
	H.						
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TL	K.	WO 03/023875	03/20/2003	PCT				
	L.							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

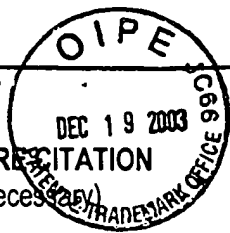
	P.	
	Q.	
	R.	
	S.	
	T.	
	U.	
	V.	

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APPLICANT(S):

BRIAN G. JOHNSON AND STEPHEN J. HUDGENS

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
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	C.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	D.							
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	F.							

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<i>R</i>	G.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 th IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003
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